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## Magnesium based Si-Ge alloys under pressure: DFT evolutionary search results

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**Abstract.** The search of minimal enthalpy structures of ternary magnesium alloys of different stoichiometry  $Mg_xSi_yGe_z$  under pressure  $P \leq 6$  GPa has been performed using the software suite USPEX implementing the evolution algorithm combined with the density functional theory (DFT) approach. The evolutionary search has yielded new possible ternary compounds of the stoichiometries  $Mg_{12}Ge_3Si$ ,  $Mg_6Ge_4Si_3$ ,  $Mg_6Ge_3Si_4$ ,  $Mg_6GeSi_3$ ,  $Mg_4Ge_3Si_2$ ,  $Mg_4Ge_3Si_2$ ,  $Mg_4SiGe$ , and  $Mg_2GeSi$ , which have negative enthalpy of formation at pressures in the range of 0 to 10 GPa and which are not substitution solutions of Ge on  $Mg_2Si$  matrix (or Si on  $Mg_2Ge$  matrix). These compounds have metallic properties and formation enthalpies comparable to those of binary silicides  $Mg_2Si$ . Phonon spectra investigations indicate that only first five of them are stable showing no imaginary frequencies.

**Keywords:**  $Mg_xSi_yGe_z$ , crystal structure, hydrostatic pressure, evolutionary search, density functional theory

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Материалы конференции  
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## Кремниевое-германиевые сплавы на основе магния: результаты эволюционного поиска из первых принципов

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**Аннотация.** С помощью пакета программ USPEX, реализующих эволюционные алгоритмы на базе теории функционала плотности, был проведен поиск оптимальных структур твердых растворов магния, олова и магния разной стехиометрии  $Mg_xSi_yGe_z$  под давлением  $P \leq 6$  ГПа. В результате эволюционного поиска обнаружены новые возможные трехкомпонентные структуры состава  $Mg_{12}Ge_3Si$ ,  $Mg_6Ge_4Si_3$ ,  $Mg_6Ge_3Si_4$ ,  $Mg_6GeSi_3$ ,  $Mg_4Ge_3Si_2$ ,  $Mg_4Ge_3Si_2$ ,  $Mg_4SiGe$ , и  $Mg_2GeSi$ , которые имеют отрицательную энтальпию формирования в диапазоне давлений  $0 < P \leq 10$  ГПа и не являются твердыми растворами замещения атомов Si атомами Ge в  $Mg_2Si$ -матрице или атомов Ge атомами Si в  $Mg_2Ge$ -матрице. Эти соединения имеют металлические свойства и их энтальпия образования соизмерима с энтальпией образования бинарных силицидов  $Mg_2Si$ . Стабильность пяти из полученных структур подтверждается расчетами их фононных спектров, в которых не наблюдается мнимых фононных мод.

**Ключевые слова:**  $Mg_xSi_yGe_z$ , кристаллическая структура, гидростатическое давление, эволюционный поиск, методы функционала плотности

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## Introduction

Since the 1960s,  $Mg_2X$  ( $X = Si, Ge, Sn$ ) compounds and their solid solutions have shown promise for thermoelectric energy conversion due to high efficiencies, high melting points, narrow band gaps, and environmental safety. These materials are used in thermal elements, infrared detectors, solar cells, and hydrogen energy storage. Despite waning interest in the early 2000s, compositional flexibility and similar crystal structures have revived interest.  $Mg_2Ge$  is soluble in  $Mg_2Si$  and *vice versa* [1–8], enhancing thermoelectric performance through improved conductivity [9]. Varying germanium concentration tailors properties for energy conversion. For example,  $Mg_2Si_{1-x}Sn_x$  with low thermal conductivity is favorable for thermoelectric energy conversion [10]. However, challenges exist in forming solid solutions and optimizing microstructure. Successful synthesis requires uniform structures [11, 12], highlighting the need for thorough investigation. Further research is needed to improve properties by exploring dopants and optimizing synthesis techniques [13].

Computational methods are crucial in material discovery, being more efficient than experiments. These computational searches allow researchers to rapidly explore a wide range of systems, uncovering novel phenomena and facilitating the discovery of new promising materials. Recent successes with two-component magnesium-based compounds suggest potential for three-component  $Mg_xSi_yGe_z$  alloys. Anti-fluorite structure is the only one considered in the analysis of magnesium stannides, as both magnesium silicide and magnesium germanide share this structural form. Evolutionary optimization has reproduced known phases and predicted new structures under high pressures. The aim of this study is to identify optimal structures in the three-component  $Mg_xSi_yGe_z$  system using modern evolutionary optimization techniques [14], and to investigate the stability of these structures both at ambient pressure conditions as well as at pressures ranging from 0 to 10 GPa.

## Calculation procedure

For evolutionary modeling of the three-component Mg-Si-Ge system, Universal Structure Predictor: Evolutionary Xtallography (USPEX) algorithms were applied in the variable composition mode [15–17]. During the evolutionary search, from 40 to 60 generations of structures were produced depending on the convergence, which was considered to be achieved when the most energetically favorable structure remained unchanged for 20 consecutive generations. Each generation contained 20 structures and the first generation contained more than 120 structures, with 4 to 32 atoms per every structure. The structures of the first generation were randomly selected from the list of 230 space groups. In the following generations, 50% of the lowest-energy structures were inherited from the previous generation, 10% of the structures were produced by lattice mutation, 10% of the structures were obtained by atom transmutation, and the remaining 30% of the structures were generated randomly. All USPEX generated structures were then relaxed using the conjugate gradient method implemented in the VASP software [18], the one-electron wave functions were expanded in a plane-wave basis with a kinetic energy cutoff of  $E_{cut} = 500$  eV. The exchange-correlation potential chosen based on the Purdue-Burke-Ernzerhof parameterization in the generalized gradient approximation [19]. Brillouin zone sampling was

performed using a Monkhorst-Pack mesh with a  $k$ -point resolution of  $\pi \times 0.1 \text{ \AA}^{-1}$ . The enthalpy at a zero temperature was determined using relationship  $F = E + PV$ , where  $E$  is the total energy,  $P$  is the external pressure, and  $V$  is the primitive cell volume.

### Results and Discussion

For calculations of three-component structures at ambient pressure conditions it is useful to carry out their studies at several pressures [20–22]. Then there are quite a lot of them compared to the calculations at ambient pressure conditions, which allows to study their  $E(P)$  dependences in more detail and to select the most stable compounds. Three pressure values of 1 GPa, 4 GPa and 6 GPa were used to calculate germanium-silicon alloys and more than five and a half thousand structures were obtained by evolutionary search. Thus, if at 6 GPa we more than a hundred structures with negative enthalpy of formation, at 4 GPa there are only two, and at 1 GPa there are only three with energy close to zero. Since too few three-component systems are stable at low pressures, the structures obtained at non-zero pressures were used for their calculation, as will be shown below.

Table shows the lattice parameters and enthalpies of formation of the most stable convex hull compounds of magnesium, silicon and germanium obtained by evolutionary methods at external hydrostatic pressures of 1, 4 and 6 GPa. At a pressure of  $P = 1 \text{ GPa}$ , the convex hull is formed by five vertices, one of which corresponds to the ternary compound  $\text{Mg}_6\text{GeSi}_3$  of space group 146 and two of which correspond to the binary silicides  $\text{Mg}_2\text{Si}$  and  $\text{Mg}_3\text{Si}_2$  of space groups 129 and 167, respectively.

Table

**Structures, corresponding to the vertices of the convex shell at pressures of 1, 4 and 6 GPa**

Pressure/ Composition	Lattice parameters	Symmetry
<b>1 GPa/</b> $\text{Mg}_6\text{Si}_3\text{Ge}$	$a = b = c = 7.46 \text{ \AA}$ , $\alpha = \beta = 90^\circ, \gamma = 120^\circ$	$R3$ (146)
<b>1 GPa/</b> $\text{Mg}_3\text{Si}_2$	$a = b = 7.44 \text{ \AA}, c = 12.22 \text{ \AA}$ , $\alpha = \beta = \gamma = 90^\circ$	$R-3C$ (167)
<b>1 GPa/</b> $\text{Mg}_2\text{Si}$	$a = b = 4.14 \text{ \AA}, c = 6.90 \text{ \AA}$ , $\alpha = \beta = \gamma = 90^\circ$	$P4/nmm$ (129)
<b>4 GPa/</b> $\text{Mg}_6\text{Si}_4\text{Ge}_3$	$a = 8.4 \text{ \AA}, b = 5.31 \text{ \AA}, c = 5.25 \text{ \AA}$ , $\alpha = 93.9^\circ, \beta = 90.2^\circ, \gamma = 95.3^\circ$	$P1(1)$
<b>4 GPa/</b> $\text{Mg}_6\text{Si}_3\text{Ge}_4$	$a = 8.46 \text{ \AA}, b = 5.34 \text{ \AA}, c = 5.26 \text{ \AA}$ , $\alpha = 93.8^\circ, \beta = 90.4^\circ, \gamma = 95.6^\circ$	$P1(1)$
<b>4 GPa/</b> $\text{Mg}_2\text{Si}$	$a = b = c = 6.23 \text{ \AA}$ , $\alpha = \beta = 90^\circ, \gamma = 120^\circ$	$Fm\bar{3}m$ (225)
<b>6 GPa/</b> $\text{Mg}_2\text{SiGe}$	$a = 4.17 \text{ \AA}, b = 3.66 \text{ \AA}, c = 5.00 \text{ \AA}$ , $\alpha = 90^\circ, \beta = 70.6^\circ, \gamma = 90^\circ$	$Pm$ (6)
<b>6 GPa/</b> $\text{Mg}_4\text{Si}_2\text{Ge}_3$	$a = 5.06 \text{ \AA}, b = 8.46 \text{ \AA}, c = 8.04 \text{ \AA}$ , $\alpha = 78.0^\circ, \beta = 90.5^\circ, \gamma = 73.3^\circ$	$P1(1)$
<b>6 GPa/</b> $\text{Mg}_6\text{Si}_3\text{Ge}$	$a = 4.95 \text{ \AA}, b = 5.68 \text{ \AA}, c = 6.59 \text{ \AA}$ , $\alpha = 76.3^\circ, \beta = 103.9^\circ, \gamma = 98.1^\circ$	$P1(1)$
<b>6 GPa/</b> $\text{Mg}_2\text{Si}$	$a = b = 4.52 \text{ \AA}, c = 5.82 \text{ \AA}$ , $\alpha = \beta = 90^\circ, \gamma = 120^\circ$	$P6_3/mmc$ (194)
<b>6 GPa/</b> $\text{MgSi}$	$a = 5.38 \text{ \AA}, b = 5.25 \text{ \AA}, c = 5.19 \text{ \AA}$ , $\alpha = 89.4^\circ, \beta = 79.7^\circ, \gamma = 111.4^\circ$	$P-1(2)$
<b>6 GPa/</b> $\text{MgSi}_3$	$a = b = 7.62 \text{ \AA}, c = 15.05 \text{ \AA}$ , $\alpha = \beta = 90^\circ, \gamma = 120^\circ$	$R-3m$ (166)

The remaining two structures, corresponding to the bulk structures of germanium and silicon, are not shown in Table and described below. At a pressure  $P = 4$  GPa, the convex hull includes bulk Ge and Si structures, two asymmetric ternary compounds  $\text{Mg}_6\text{Ge}_4\text{Si}_3$  and  $\text{Mg}_6\text{Ge}_3\text{Si}_4$ , and a binary silicide  $\text{Mg}_2\text{Si}$  of correctly defined space symmetry group 225. At a pressure  $P = 6$  GPa, the convex hull is formed by three ternary alloys  $\text{Mg}_4\text{Si}_2\text{Ge}_3$ ,  $\text{Mg}_6\text{Si}_3\text{Ge}$ ,  $\text{Mg}_2\text{SiGe}$  and three binary silicides of different stoichiometries from 2/3 of Mg and 1/3 of Si ( $\text{Mg}_2\text{Si}$ ) to 1/4 of Mg and 3/4 of Si ( $\text{MgSi}_3$ ), in addition to the bulk Ge and Si structures. The ternary alloys at this pressure have symmetries down to 1 (P1) for  $\text{Mg}_4\text{Si}_2\text{Ge}_3$  and  $\text{Mg}_6\text{Si}_3\text{Ge}$  and 6 (Pm) for  $\text{Mg}_2\text{SiGe}$ . The binary silicides have symmetries as low as 2 for  $\text{MgSi}$  and as high as 166 for  $\text{MgSi}_3$  and 194 for  $\text{Mg}_2\text{Si}$ .

For a detailed study of the stability of energetically favorable structures under various pressures, Table results were recalculated for pressures from 0 to 10 GPa with geometry re-optimization. Fig. shows the most stable structures with negative formation enthalpy obtained by optimizing evolutionary search results. It also includes calculations for ternary compounds formed by Sn $\rightarrow$ Ge substitution or rearrangement in Mg-Si-Sn structures [23], as well as optimized convex hull structures from Si $\leftrightarrow$ Ge atom exchange. Surprisingly, these structures are more stable than those obtained from evolutionary search. For example,  $\text{Mg}_6\text{SiGe}_3$ , derived from  $\text{Mg}_6\text{Si}_3\text{Ge}$  by Si $\leftrightarrow$ Ge atoms exchange and relaxation, is the most stable structure in the 1.15–10 GPa range. At ambient

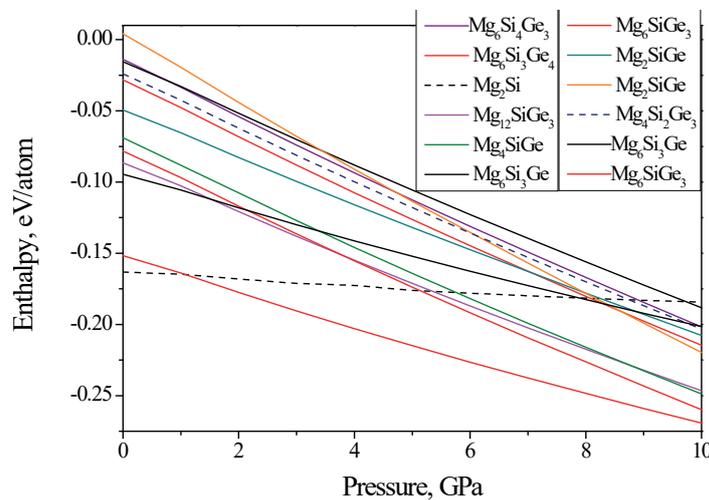


Fig. Enthalpy-pressure  $E(P)$  dependence for the most energetically favorable crystal structures obtained by optimizing the results of the evolutionary search and their corresponding derivatives from the Mg-Si-Sn structures (see text for details)

pressure, only the cubic anti-fluorite  $\text{Mg}_2\text{Si}$  structure ( $\text{Fm}\bar{3}\text{m}$  symmetry) is more stable than them. Linear extrapolation from Fig. suggests  $\text{Mg}_6\text{Si}_3\text{Ge}$  will become less stable at around 11.5 GPa, with  $\text{Mg}_4\text{SiGe}$  being the most stable above 15 GPa.  $\text{Mg}_{12}\text{SiGe}_3$  structure ( $\text{I4}/\text{mmm}$  symmetry) was created from  $\text{Mg}_{12}\text{SiSn}_3$  by replacing Sn atoms with Ge ones. Another structure,  $\text{Mg}_4\text{SiGe}$  ( $P-1$  symmetry), was derived similarly from  $\text{Mg}_4\text{SiSn}$ . At pressures  $P > 44$  GPa,  $\text{Mg}_4\text{SiGe}$  becomes more stable than both  $\text{Mg}_6\text{SiGe}_3$  structures.  $\text{Mg}_6\text{Si}_3\text{Ge}$  structures from evolutionary search, shown on Fig., are lower in enthalpy than  $\text{Mg}_2\text{Si}$  one at pressures  $P > 8$  GPa, but higher than  $\text{Mg}_6\text{Si}_3\text{Ge}_4$  and  $\text{Mg}_2\text{SiGe}$  ones at  $P = 4$  GPa and  $P = 6$  GPa, respectively. The latter structures may become more stable at higher pressures based on linear extrapolation of  $E(P)$  dependencies. Therefore, their electronic structures should also be examined.

In order to investigate the conductive properties of three-component systems at ambient pressure conditions, the band structures and total density of states of the most energetically favorable compounds  $\text{Mg}_x\text{Si}_y\text{Ge}_z$  have been calculated. All of the alloys considered have states at the Fermi level, indicating that they all exhibit metallic properties to some extent, unlike the binary compounds  $\text{Mg}_2\text{Si}$  and  $\text{Mg}_2\text{Ge}$ , which are semiconductors under normal conditions.

To verify the dynamical stability of three-component alloys, phonon dispersion curves at ambient pressure conditions have been calculated for most of the lowest energy structures – see additive materials in [24]). This analysis was conducted by deriving force constants from atomic

forces and displacements, as implemented in the PHONOPY code [25, 26]. The results indicate that the phonon dispersion curves do not exhibit any imaginary frequencies for  $\text{Mg}_{12}\text{Ge}_3\text{Si}$ ,  $\text{Mg}_6\text{Ge}_4\text{Si}_3$ ,  $\text{Mg}_6\text{Ge}_3\text{Si}_4$ , triclinic  $\text{Mg}_6\text{SiGe}_3$ ,  $\text{Mg}_4\text{Ge}_3\text{Si}_2$ , thereby confirming the stability of the respective compounds. In contrast, the spectra of hexagonal  $\text{Mg}_6\text{SiGe}_3$ , orthorhombic  $\text{Mg}_2\text{SiGe}$  and monoclinic  $\text{Mg}_4\text{SiGe}$  structures displays a pronounced negative dip near special  $k$ -points (see additive materials in [24]), providing evidence for their instability relative to the other ones. Nevertheless, structures energetically favorable at high pressures non-symmetric  $\text{Mg}_6\text{SiGe}_3$  and cubic  $\text{Mg}_{12}\text{SiGe}_3$  are still stable, which makes it possible for them to exist along with the known  $\text{Mg}_2\text{Si}$  and  $\text{Mg}_2\text{Ge}$  structures.

### Conclusion

The results of the evolutionary search of three-component systems allowed to obtain new possible structures of the stoichiometries  $\text{Mg}_6\text{SiGe}_3$ ,  $\text{Mg}_6\text{GeSi}_3$ ,  $\text{Mg}_{12}\text{Ge}_3\text{Si}$ ,  $\text{Mg}_4\text{SiGe}$ ,  $\text{Mg}_4\text{Ge}_3\text{Si}_2$ ,  $\text{Mg}_2\text{SiGe}$ ,  $\text{Mg}_6\text{Si}_4\text{Ge}_3$  and  $\text{Mg}_6\text{Si}_3\text{Ge}_4$  with the ternary compound  $\text{Mg}_{12}\text{Ge}_3\text{Si}$  being the most stable one. All of them have a negative enthalpy of formation, comparable to the enthalpy of formation of binary structures  $\text{Mg}_2\text{Si}$  and  $\text{Mg}_2\text{Ge}$  in the studied pressure range  $0 < P \leq 10$  GPa. Phonon dispersion and density of states calculations confirmed the dynamical stability and metallic properties of the newly identified ternary alloys besides the  $\text{Mg}_2\text{SiGe}$ ,  $\text{Mg}_4\text{SiGe}$  and  $\text{Mg}_6\text{SiGe}_3$  ones. Density of states calculations indicate the ternary alloys exhibit metallic properties, unlike the binary silicides and germanides.

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